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roducts	Home > 2N3245 (#23686) 2N3245 (#23686)								Related Links
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	Electrical Rating	Symbo	l Mir		Гур	Max	Unit		Sales Contacts RFQ/Samples
	Collector to Emitter Saturation Voltage	V _{CE(sal})			0.60	V		RFQ/Samples
	DC Current Gain	HFE	30.	00		90.00			
	Maximum Electrical Rating		Symbol	Min	Vlin Typ	Max	Unit		
	Breakdown Voltage, Collector-Base (Emitter Open)		V _{BR(CBO)}		_	50.00	V		
	Collector Current (dc)					1.00	А		
	Collector-Emitter Voltage (Base Open)		$V_{\rm CEO}$			50.00	V	V	
	Emitter-Base Voltage (Collector Open)		V _{EBO}			5.00	V		
	Power Dissipation, Total		PT			5.00	5.00 W		
	This part can be found in the following product Discretes Transistors BJT(BiPolar Junction Tran Non-Radiation Hardened Devices Transistors B	nsistor)	PNP Trar		tor) 🕨 F	NPTransis	stor		

